

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	Ī
DC Characteristics			•	•	•
Collector-emitter breakdown voltage	V _{(BR)CEO}	300	-	-	V
<i>I</i> _C = 1 mA, <i>I</i> _B = 0					
Collector-base breakdown voltage	V _{(BR)CBO}	300	-	-	
<i>I</i> _C = 100 μA, <i>I</i> _E = 0					
Emitter-base breakdown voltage	V _{(BR)EBO}	5	-	-	
I _E = 100 μA, I _C = 0					
Collector-base cutoff current	I _{CBO}				μA
$V_{\rm CB}$ = 250 V, $I_{\rm E}$ = 0		-	-	0.1	
$V_{\rm CB}$ = 250 V, $I_{\rm E}$ = 0 , $T_{\rm A}$ = 150 °C		-	-	20	
Emitter-base cutoff current	I _{EBO}	-	-	100	nA
$V_{\rm EB}$ = 5 V, $I_{\rm C}$ = 0					
DC current gain ¹⁾	h _{FE}				-
<i>I</i> _C = 1 mA, <i>V</i> _{CE} = 10 V		25	-	-	
<i>I</i> _C = 10 mA, <i>V</i> _{CE} = 10 V		40	-	-	
<i>I</i> _C = 30 mA, <i>V</i> _{CE} = 10 V		30	-	-	
Collector-emitter saturation voltage ¹⁾	V _{CEsat}	-	-	0.5	V
$I_{\rm C}$ = 20 mA, $I_{\rm B}$ = 2 mA					
Base emitter saturation voltage ¹⁾	V _{BEsat}	-	-	0.9	
<i>I</i> _C = 20 mA, <i>I</i> _B = 2 mA					
AC Characteristics					
Transition frequency	f_	_	100	_	MH ₂

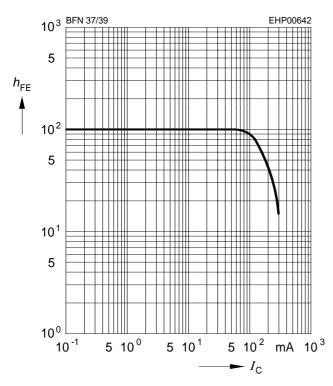
Transition frequency	f _T	-	100	-	MHz
<i>I</i> _C = 20 MHz, <i>V</i> _{CE} = 10 V, <i>f</i> = 100 MHz					
Collector-base capacitance	C _{cb}	-	2.5	-	pF
V _{CB} = 30 V, <i>f</i> = 1 MHz					

¹Pulse test: t < 300 μ s; D < 2%

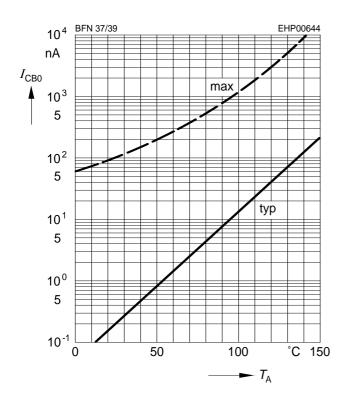


DC current gain $h_{\text{FE}} = f(I_{\text{C}})$

*V*_{CE} = 10 V

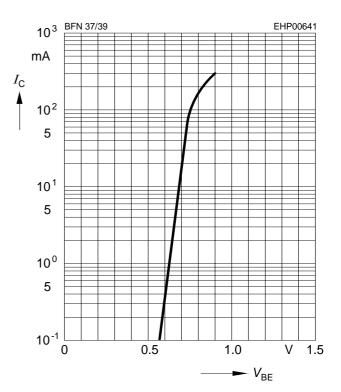


Collector cutoff current $I_{CBO} = f(T_A)$ $V_{CBO} = 200 \text{ V}$

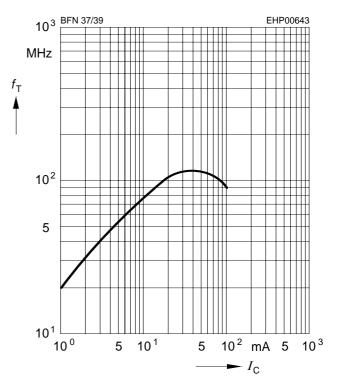


Collector current $I_{\rm C} = f(V_{\rm BE})$

 $V_{\rm CE}$ = 10V

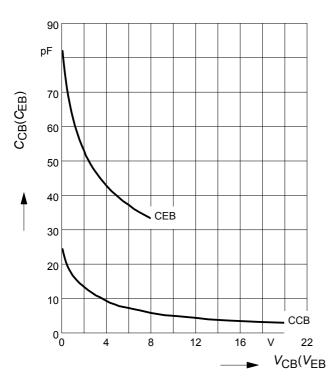


Transition frequency $f_{\rm T} = f(I_{\rm C})$ $V_{\rm CE} = 10 \text{ V}$



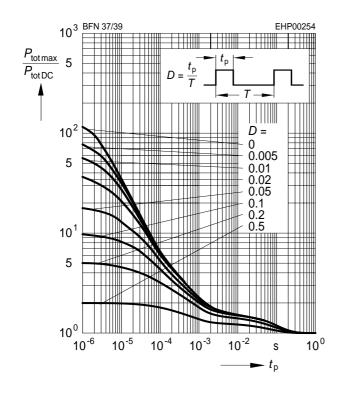


Collector-base capacitance $C_{cb} = f(V_{CB})$ Emitter-base capacitance $C_{eb} = f(V_{EB})$

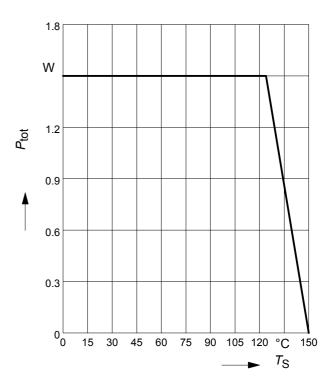


Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$

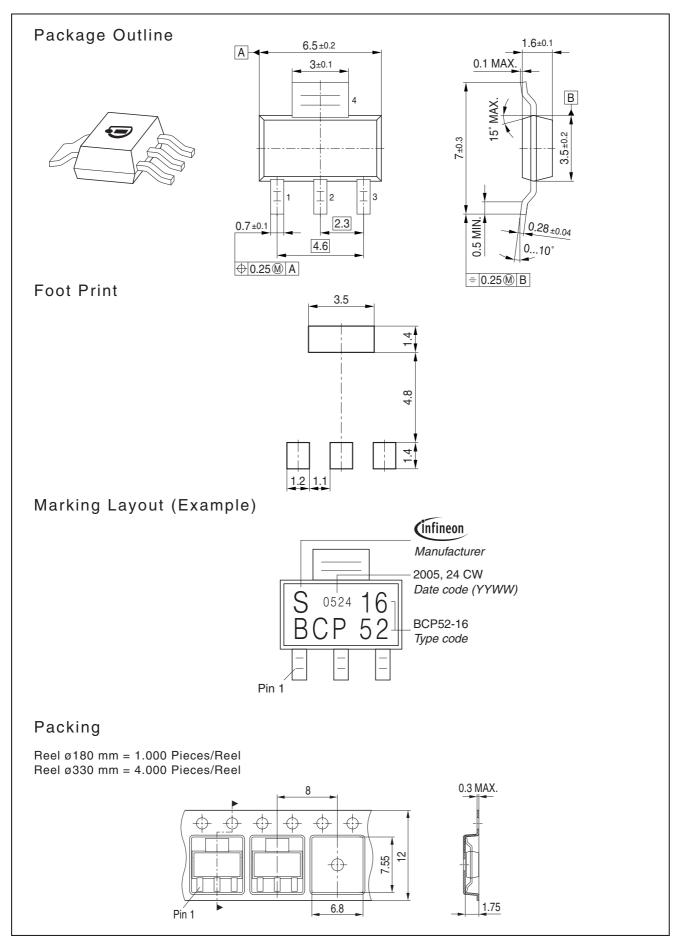


Total power dissipation $P_{tot} = f(T_S)$



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